DUAL OPERATIONAL AMPLIFIERS

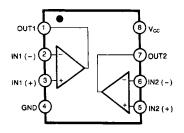
The LM258 series consists of four independent, high gain, internally Frequency compensated operational amplifiers which were designed specifically to operate from a single power supply over a wide range of voltage.

Operation from split power supplies is also possible and the low power Supply current drain is independent of the magnitude of the power Supply voltage. Application areas include transducer amplifier, DC gain blocks and all the conventional OP amp circuits which now can be easily implemented in single 8 SOP power supply system.

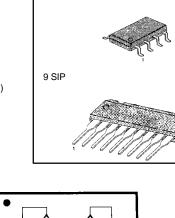
FEATURES

- · Internally frequency compensated for unity gain
- Large DC voltage gain: 100dB
- Wide power supply range: LM258/A, LM358/A: 3V~32V (or ±1.5V~16V) LM2904: 3V~26V (or ±1.5V~13V)
- Input common-mode voltage range Includes ground
- Large output voltage swing: 0V DC to Vcc 1.5V DC
- Power drain suitable for battery operation.

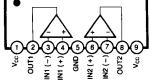
BLOCK DIAGRAM



SCHEMATIC DIAGRAM (One section only)



8 DIP



ORDERING INFORMATION

Q5 Q6 Q12 Q17 020 0: Ô۶ IN(C1 Ò łŀ 0-O OUT IN(+)Q21 h 01 Q1 Q10 01 09 0

Device	Package	Operating Temperature
LM358N	8 DIP	
LM358AN	0 DIF	
LM358S	9 SIP	0 ~ + 70°C
LM358AS	9 OIF	0~+700
LM358M	8 SOP	
LM358AM	0 30F	
LM258N	8 DIP	
LM258AN	0 DIF	
LM258S	9 SIP	-25 ~ + 85 °C
LM258AS	9 OF	-23 ~ + 03 0
LM258M	8 SOP	
LM258AM	0 30F	
LM2904N	8 DIP	
LM2904S	9 SIP	-40 ~ + 85 °C
LM2904M	8 SOP	



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Rev. B

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	LM258/LM258A	LM358/LM358A	LM2904	Unit
Supply Voltage	V _{cc}	±16 or 32	±16 or 32	±13 or 26	V
Differential Input Voltage	V _{I(DIFF)}	32	32	26	V
Input Voltage	VI	-0.3 to +32	-0.3 to +32	-0.3 to +26	V
Output Short Circuit to GND			0 1	0 1	
V _{CC} ≤V, T _A = 25 °C(One Amp)		Continuous	Continuous	Continuous	
Operating Temperature Range	T _{OPR}	-25 ~ + 85	0 ~ + 70	-40 ~ + 85	°C
Storage Temperature Range	T _{STG}	-65 ~ + 150	-65 ~ + 150	-65 ~ + 150	°C

ELECTRICAL CHARACTERISTICS

(V_{CC} = 5.0V, V_{EE} = GND, T = 25 $^{\circ}C$, unless otherwise specified)

				LM258		I	_M358	8	I	Unit			
Characteristic	Symbol	Test Conditions		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	onn
Input Offset Voltage	V _{IO}	$V_{CM} = 0V$ to V_{CC} -1.5V $V_{O(P)} = 1.4V$, $R_S = 0\Omega$	$V_{CM} = 0V$ to V_{CC} -1.5V $V_{O(P)} = 1.4V, R_S = 0\Omega$		2.9	5.0		2.9	7.0		2.9	7.0	mV
Input Offset Current	l _{io}				3	30		5	50		5	50	nA
Input Bias Current	IBIAS				45	150		45	250		45	250	nA
Input Common-Mode Voltage Range	V _{I(R)}	V _{CC} = 30V (KA2904, V _{CC} = 26V)		0		V _{cc} -1.5	0		V _{CC} -1.5	0		V _{CC} -1.5	V
Supply Current	I _{cc}	$R_L = \infty$, $V_{CC} = 30V$ (KA2902, $V_{CC} = 26V$)			0.8	2.0		0.8	2.0		0.8	2.0	mA
		$R_L = \infty$, over full tempe	erature range		0.5	1.2		0.5	1.2		0.5	1.2	mA
Large Signal Voltage Gain	Gv	$V_{CC} = 15V, R_L \ge 2K\Omega$ $V_{O(P)} = 1V \text{ to } 11V$		50	100		25	100		25	100		V/mV
	V _{O(H)}	$V_{CC} = 30V$	$R_L = 2K\Omega$	26			26			22			V
Output Voltage Swing	V _{O(L)}	V _{CC} = 26V for 2904	$R_L = 10 K\Omega$	27	28		27	28		23	24		V
	• O(L)	$V_{CC} = 5V, R_L \ge 10K\Omega$			5	20		5	20		5	100	mV
Common-Mode Rejection Ratio	CMRR			70	85		65	80		50	80		dB
Power Supply Rejection Ratio	PSRR			65	100		65	100		50	100		dB
Channel Separation	CS	f = 1KHz to 20KHz			120			120			120		dB
Short Circuit to GND	I _{SC}				40	60		40	60		40	60	mA
	I _{SOURCE}			10	30		10	30		10	30		mA
Output Current	I _{SINK}	$V_{I(+)} = 0V, V_{I(-)} = 1V$ $V_{CC} = 15V, V_{O(P)} = 2V$		10	15		10	15		10	15		mA
		$V_{I(+)} = 0V, V_{I(-)} = 1V$ $V_{CC} = 15V, V_{O(P)} = 200$)mA	12	100		12	100					μΑ
Differential Input Voltage	$V_{\text{I}(\text{DIFF})}$					V_{cc}			V_{cc}			V_{cc}	V



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ELECTRICAL CHARACTERISTICS

(V_{CC}=5.0V, V_{EE}=GND, unless otherwise specified) The following specification apply over the range of - 25 °C \leq T_A \leq + 85 °C for the KA258; and the 0 °C \leq T_A \leq + 70 °C for the LM358; and the -40 °C \leq T_A \leq +85 °C for the LM2904

Characteristic	Ourseland.			LM258			LM358			LM2904			Unit
Characteristic	Symbol			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Input Offset Voltage	VIO	$V_{CM} = 0V \text{ to } V_{CC} = 1.$ $V_{O(P)} = 1.4V, R_S = 00$				7.0			9.0			10.0	mV
Input Offset Voltage Drift	V _{IO}	$R_{S} = 0\Omega$			7.0			7.0			7.0		μV/°C
Input Offset Current	I _{IO}					100			150		45	200	nA
Input Offset Current Drift	$\Delta I_{\rm IO}/\Delta T$				10			10			10		pA/°C
Input Bias Current	I _{BIAS}				40	300		40	500		40	500	nA
Input Common-Mode Voltage Range	V _{I(R)}	V _{CC} = 30V (KA2904,V _{CC} = 26V)		0		V _{CC} =2.0	0		V _{CC} =2.0	0		V _{CC} =2.0	V
Large Signal Voltage Gain	Gv	V _{CC} = 15V, R _L ≥2.0KΩ V _{O(P)} = 1V to 11V	2	25			15			15			V/mV
	N/	$V_{CC} = 30V$	$R_L = 2K\Omega$	26			26			26			V
Output Voltage Swing	V _{O(H)}	V _{CC} = 26V for 2904	$R_L = 10K\Omega$	27	28		27	28		27	28		V
	V _{O(L)}	V _{CC} = 5V, R _L ≥10KΩ			5	20		5	20		5	20	mV
Output Current	ISOURCE	$V_{I(+)} = 1V, V_{I(-)} = 0V$ $V_{CC} = 15V, V_{O(P)} = 2V$	/	10	30		10	30		10	30		mA
Output Current	I _{SINK}		/	5	8		5	9		5	9		mA
Differential Input Voltage	$V_{\text{I}(\text{DIFF})}$					V _{CC}			V _{cc}			V_{CC}	V



ELECTRICAL CHARACTERISTICS

(V_{CC} = 5.0V. V_{EE}=GND. T_A=25\,^{\circ}C, unless otherwise specified)

	Cumb al		L	M258	A	L	Unit		
Characteristic	Symbol	Test Conditions	Min	Тур	Max	MIn	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$\label{eq:VCM} \begin{split} V_{CM} &= 0V \text{ to } V_{CC} = 1.5V \\ V_{O(P)} &= 1.4V, \ R_S = 0\Omega \end{split}$		1.0	3.0		2.0	3.0	mV
Input Offset Current	I _{IO}			2	15		5	30	nA
Input Bias Current	I _{BIAS}			40	80		45	100	nA
Input Common-Mode Voltage Range	V _{I(R)}	$V_{CC} = 30V$	0		V _{CC} =1.5	0		V _{CC} =1.5	V
Quarte Quart		$R_L = \infty, V_{CC} = 30V$		0.8	2.0		0.8	2.0	mA
Supply Current	Icc	$RL = \infty$, over full temperature range		0.5	1.2		0.5	1.2	mA
Large Signal Voltage Gain	Gv	$V_{CC} = 15V, R_L \ge 2K\Omega$ $V_O = 1V$ to 11V	50	100		25	100		V/mV
	V	$V_{CC} = 30V$ $R_1 = 2K\Omega$	26			26			V
Output Voltage Swing	V _{OH}	$V_{CC} = 26V$ for 2904 $R_{L} = 10K\Omega$	27	28		27	28		V
	V _{O(L)}	$V_{CC} = 5V, R_L \ge 10K\Omega$		5	20		5	20	mV
Common-Mode Rejection Ratio	CMRR		70	85		65	85		dB
Power Supply Rejection Ratio	PSRR		65	100		65	100		dB
Channel Separation	CS	f = 1KHz to 20KHz		120			120		dB
Short Circuit to GND	I _{SC}			40	60		40	60	mA
	I _{SOURCE}	$V_{I(+)} = 1V, V_{I(-)} = 0V$ $V_{CC} = 15V, V_{O(P)} = 2V$	20	30		20	30		mA
Output Current	I _{SINK}	$V_{I(+)} = 1V, V_{I(-)} = 0V$ $V_{CC} = 15V, V_{O(P)} = 2V$	10	15		10	15		mA
	ISINK	$V_{in +} = 0V, V_{in -} = 1V$ $V_{O(P)} = 200mV$	12	100		12	100		μΑ
Differential Input Voltage	VI(DIFF)				Vcc			Vcc	V



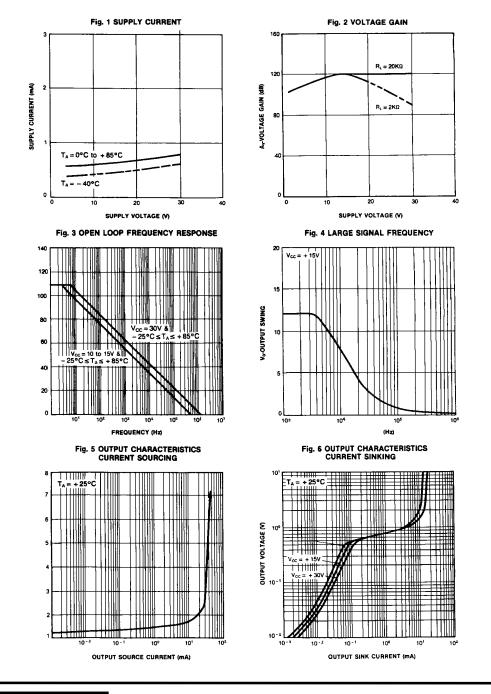
ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0V$, $V_{EE} = GND$. unless otherwise specified)

The following specification apply over the range of -25 °C \leq T $_{A}$ \leq +85 °C for the LM258A; and the 0 °C \leq T $_{A}$ \leq +70 °C for the LM358A

Ohannatariatia		Toot Co	Test Conditions		LM258/	١		LM358/	1		
Characteristic	Symbol	Test Conditions		Min	Тур	Max	Min	Тур	Max	Unit	
Input Offset Voltage	V _{IO}	$V_{CM} = 0V$ to $V_{CC} = 1.5V$ $V_{O(P)} = 1.4V$, $R_S = 0\Omega$				4.0			5.0	mV	
Input Offset Voltage Drift	$\Delta V_{IO} / \Delta T$				7.0	15		7.0	20	μV/°C	
Input Offset Current	l _{io}					30			75	nA	
Input Offset Current Drift	$\Delta I_{IO}/\Delta T$				10	200		10	300	pA/ °C	
Input Bias Current	IBIAS				40	100		40	200	nA	
Input Common-Mode Voltage Range	V _{I(R)}	$V_{CC} = 30V$		0		Vcc =2.0	0		Vcc =2.0	V	
	V _{O(H)}	$V_{CC} = 30V$	$R_L = 2K\Omega$	26			26			V	
Output Voltage Swing	• O(H)	$V_{CC} = 30V$	$R_L = 10K\Omega$	27	28		27	28		V	
	V _{O(L)}	$V_{CC} = 5V, R_{L^2}$	≥10KΩ		5	20		5	20	mV	
Large Signal Voltage Gain	G_{V}	$V_{CC} = 15V, R_L \ge 2.0 K\Omega$ $V_{O(P)} = 1V \text{ to } 11V$		25			15			V/mV	
Output Current	I _{SOURCE}			10	30		10	30		mA	
	I _{SINK}	$V_{I(+)} = 1V, V_{I(-)}$ $V_{CC} = 15V, V_{CC}$,	5	9		5	9		mA	
Differential Input Voltage	V _{I(DIFF)}					V _{cc}			V _{CC}	V	

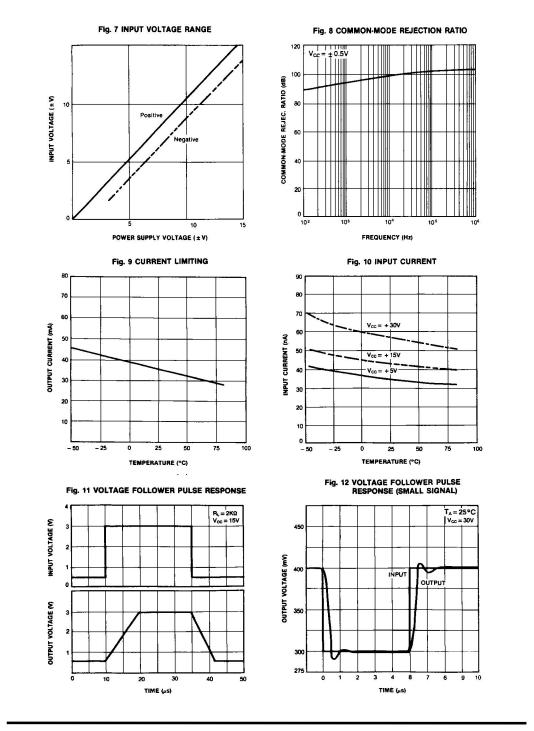


TYPICAL PERFORMANCE CHARACTERISTICS





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